Patent
Attorney's Docket No. 030681-366

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	)	
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Kyo-yeol LEE	)	Group Art Unit: Unassigned
	)	
Application No.: New Application	)	Examiner: Unassigned
	)	
Filed: Herewith	)	
	)	
For: METHOD FOR FABRICATING GROUP III-V COMPOUND SEMICONDUCTOR SUBSTRATE	)	

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination on the merits, kindly amend the above-captioned application as follows:

IN THE SPECIFICATION:

Kindly add the following paragraph on page 1, after the title of the invention and before the "Background of the Invention," --Priority is claimed to Patent Application Number 2001-11153 filed in the Republic of Korea on March 5, 2001 herein incorporated by reference.--

IN THE CLAIMS:

Kindly replace claims 7, 12 and 26 as follows:

7. (Amended) The method of claim 1, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

12. (Amended) The method of claim 1, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

26. (Amended) The method of claim 1, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

Kindly add new claims 28-40 as follows:

--28. (New) The method of claim 4, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

29. (New) The method of claim 5, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

30. (New) The method of claim 6, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

31. (New) The method of claim 4, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

32. (New) The method of claim 5, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

33. (New) The method of claim 6, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

34. (New) The method of claim 2, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

35. (New) The method of claim 15, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

36. (New) The method of claim 16, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

37. (New) The method of claim 18, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

38. (New) The method of claim 20, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

39. (New) The method of claim 23, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

40. (New) The method of claim 24, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.--

REMARKS

Claims 7, 12 and 26 have been amended and claims 28-40 have been added to remove multiple dependency from the claims. The priority document has been incorporated by reference. Favorable action on the merits is respectfully requested.

Respectfully submitted,

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Date: March 4, 2002

Attachment to Amendment

Marked-up Claims

7. (Amended) The method of claim 1, [4, 5, or 6,] wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

12. (Amended) The method of claim 1, [4, 5, or 6,] wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

26. (Amended) The method of claim 1, [2, 15, 16, 18, 20, 23, or 24,] wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.